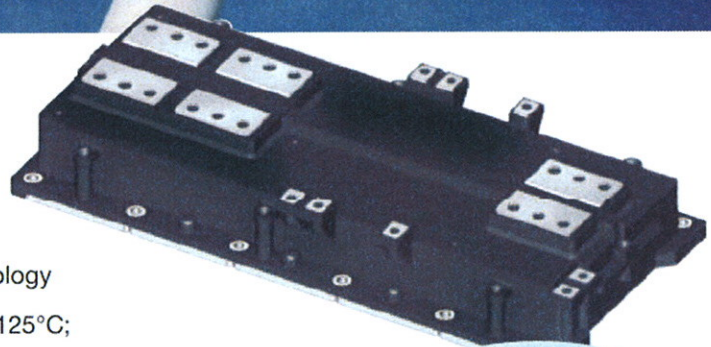


1.04

Mega Power Dual IGBT Modules (with 6th Gen. IGBT Chips)



For
Mega Power Dual
IGBT Modules (NF-Series)
please refer to
page 17/18

1

Application

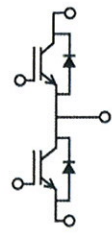
High Power Energy Conversion

Features

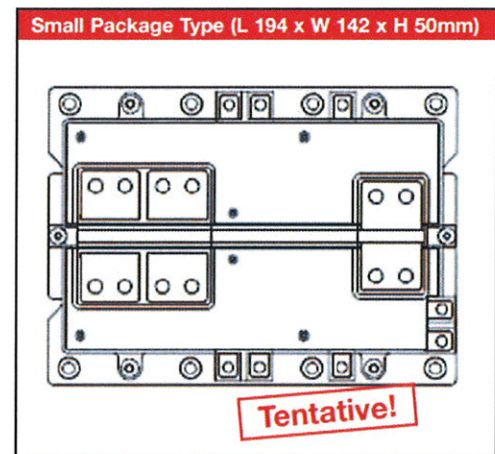
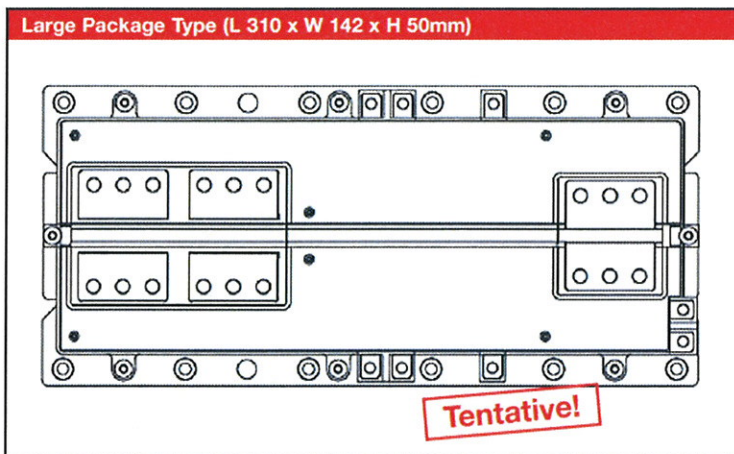
- 6th Generation IGBT with CSTBT™ Chip Technology
- For 1200V modules: $V_{CE(sat)} = 1.7V(\text{typ}) @ T_j = 125^\circ\text{C}$; wide SOA @ $V_{CC} = 900V$
- For 1700V modules: $V_{CE(sat)} = 2.2V(\text{typ}) @ T_j = 125^\circ\text{C}$; wide SOA @ $V_{CC} = 1200V$
- $T_{j(max)} = 175^\circ\text{C}$
- New solderless Al-baseplate → high ΔT_c temperature cycling capability
- Wide internal chip layout → low $R_{th(j-f)}$
- Minimized internal package inductance $L_{int} < 10nH$ (package size B)
- AC and DC main terminals separated → easy DC-bus design
- Multi-hole main terminals → low contact resistance and reliable long-term electrical connection
- Integrated NTC for T_c -sensing
- Auxiliary C-terminals available for P- and N-side IGBT

1.04 Mega Power Dual IGBT Modules (with 6th Gen. IGBT Chips)

Line-up

Symbol	Package	Circuit Diagram	Size V_{CES} (V)	A		B	
				I_C (A)			
				1100	1500	1800	2500
D			1200		CM1500DY-24S		CM2500DY-24S
			1700	CM1100DY-34S		CM1800DY-34S	

under development



Notes

1